

CMOS LDO Regulator Series for Portable Equipments





Standard CMOS LDO Regulators

BHULFB1V	VG series,	$BH ld_{ld_{}}$	FB1WHFV	series,
BH 🗌 🗆 LB1V	VG series,	BH 🗆	LB1WHFV	series

Large Current 300mA CMOS LDO Regulators

RH		MA	3/V/F	1E//	Series
ВΠ	1 11 1	IVI	SVVI	TF V	oei ies

No.09020EBT02

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The BH FB1W, BH LB1W and BH MA3W series are low dropout CMOS regulators with 150 mA and 300 mA output that have ±1% high accuracy output voltage.

The BH FB1W series combines 40μA low current consumption and a 70 dB high ripple rejection ratio by utilizing output level CMOS technology. The components can be easily mounted into the small standard SSOP5 and the ultra-small HVSOF5/HVSOF6 packages.

Features

- 1) High accuracy output voltage: ±1%
- 2) High ripple rejection ratio: 70 dB (BH FB1WHFV/WG, BH LB1WHFV/WG)
- 3) Low dropout voltage: 60 mV (when current is 100 mA) (BH MA3WHFV)
- 4) Stable with ceramic output capacitors
- 5) Low Bias current : 40µA (Io = 50 mA) (BH□□FB1WHFV/WG)
- 6) Output voltage ON/OFF control
- 7) Built-in over-current protection and thermal shutdown circuits
- 8) Ultra-small power package: HVSOF5 (BH FB1WHFV, BH LB1WHFV)
- 9) Ultra-small power package: HVSOF6 (BH MA3WHFV)

Applications

Battery-driven portable devices and etc.

Line up

■ 150mA BH ☐ FB1W and BH ☐ LB1W Series

Part Number	1.5	1.8	1.85	2.5	2.8	2.9	3.0	3.1	3.3	Package
BH□□FB1WG	-	-	-	~	~	~	~	~	~	SSOP5
BH□□FB1WHFV	-	-	-	~	~	~	~	~	~	HVSOF5
BHLB1WG	~	~	-	-	-	-	-	-	-	SSOP5
BH□□LB1WHFV	~	~	~	_	_	-	_	_	_	HVSOF5

■ 300mA BH□□MA3WHFV series

Part Number	1.5	1.8	2.5	2.8	2.9	3.0	3.1	3.3	Package
BH MA3WHFV	~	~	~	~	~	~	~	~	HVSOF6

Symbol	Details								
	Output Voltage Designation								
		Output Voltage (V)		Output Voltage (V)					
	15	1.5V (Typ.)	29	2.9V (Typ.)					
а	18	1.8V (Typ.)	30	3.0V (Typ.)					
	1J	1.85V (Typ.)	31	3.1V (Typ.)					
	25	2.5V (Typ.)	33	3.3V (Typ.)					
	28	2.8V (Typ.)							
b	Package:	G:SSOP5	HFV: HVS	OF5					

Symbol	Details										
	(Output Voltage Designation									
		Output Voltage (V)		Output Voltage (V)							
	15	1.5V (Typ.)	29	2.9V (Typ.)							
а	18	1.8V (Typ.)	30	3.0V (Typ.)							
	25	2.5V (Typ.)	31	3.1V (Typ.)							
	28	2.8V (Typ.)	33	3.3V (Typ.)							
b	Package:	HFV: HVSC	DF6								

Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit	
Applied supply voltage	VMAX	-0.3 ~ +6.5	V	
		680 *1(HVSOF6)		
Power dissipation	Pd	410 *2(HVSOF5)	mW	
		540 *3(SSOP5)		
Operating temperature range	Topr	-40*4 ~ +85	°C	
Storage temperature range	Tstg	-55 ~ +125	°C	

^{* 1} Derated at 6.8mW/°C for temperature above Ta = 25°C, when mounted on a glass epoxy PCB (70 mm X 1.6 mm). * 2 Derated at 4.1mW/°C for temperature above Ta = 25°C, when mounted on a glass epoxy PCB (70 mm X 1.6 mm). * 3 Derated at 5.4mW/°C for temperature above Ta = 25°C, when mounted on a glass epoxy PCB (70 mm X 1.6 mm). * 4 BH□□FB1W series: -30°C and up.

Recommended operating range

Parameter		Symbol	Min.	Тур.	Max.	Unit
Power supply voltage		VIN	2.5	_	5.5	V
	BHMA3W		-	-	300	mA
Output current	BH□□FB1W	IOUT	_	_	150	mA
	BH□□LB1W		_	-	150	mA

Recommended operating conditions

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Input capacitor	CIN	0.1 *1	_	_	μF	Ceramic capacitor recommended
Output capacitor	Co	1.0 *2	_	-	μF	Ceramic capacitor recommended
Noise decrease capacitor	Cn	-	0.01	0.22	μF	Ceramic capacitor recommended

■ Electrical characteristics (Unless otherwise noted, Ta=25°C, VIN=VOUT+1V*2, STBY=1.5V, CIN=0.1µF, Co=1µF)

■BH□□FB1WI	■BH□□FB1WHFV/WG , BH□□LB1WHFV/WG									
Paramet	er	Symbol	Min.	Тур.	Max.	Unit	Conditions			
Output voltage*1		Vout	Vout x 0.99	Vout	Vоит x 1.01	V	Iout=1mA			
Circuit current		I GND	_	40	70	μΑ	Iouт=50mA			
Circuit current (S	TBY)	I STBY	-	-	1.0	μΑ	STBY=0V			
Ripple rejection ra	atio	RR	_	70	_	dB	VRR=-20dBv, fRR=1kHz, Iout=10mA			
Load response 1		LTV1	_	50	_	mV	IOUT=1mA to 30mA			
Load response 2		LTV2	-	50	_	mV	IOUT=30mA to 1mA			
Dropout voltage«	3	VSAT	-	250	450	mV	VIN=0.98 X VOUT, IOUT=100mA			
Line regulation		VDL1	_	2	20	mV	VIN=VOUT+0.5V to 5.5V *4			
Load regulation		VDL01	_	10	30	mV	IOUT=1mA to 100mA			
Over current protection I	limit current*3	ILMAX	_	250	-	mA	Vo=Vout X 0.98			
Short current*3		I SHORT	_	50	_	mA	Vo=0V			
STBY pull-down i	resistor	RSTB	550	1100	2200	k				
STBY	ON	VSTBH	1.5	_	Vin	V				
control voltage	OFF	VSTBL	-0.3	_	0.3	V				

^{*} This product is not designed for protection against radio active rays.
*1 BH15, 18LB1WHFVWG: ±25 mV precision
*2 BH15, 18LB1WHFVWG: VIN = 3.5 V

■ Electrical characteristics (Unless otherwise noted, Ta=25°C, VIN=VouT+1V*4, STBY=1.5V, CIN=1µF, Co=1µF)

■BH□□MA3WHFV

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Output voltage*1	Vout	Vout x 0.99	Vout	Vоит x 1.01	V	Iout=1mA
Circuit current	I GND	-	65	95	μA	IOUT=1mA
Circuit current (STBY)	I STBY	-	-	1.0	μA	STBY=0V
Ripple rejection ratio	RR	-	60	_	dB	VRR=-20dBv, fRR=1kHz, IouT=10mA
Dropout voltage*2	VSAT1	-	60	90	mV	VIN=0.98 X VOUT, IOUT=100mA
Line regulation	VDL1	-	2	20	mV	VIN=VOUT+0.5V to 5.5V *3
Load regulation 1	VDL01	-	6	30	mV	IOUT=1mA to 100mA
Load regulation 2	VDL02	-	18	90	mV	IOUT=1mA to 300mA
Output voltage temperature	ΔVουτ/ΔΤ	_	±100	_	ppm/°C	Iоuт=1mA, Ta=-40 to +85°С
Over current protection limit current	ILMAX	-	600	_	mA	Vo=Vout X 0.85
Short current	I SHORT	-	100	_	mA	Vo=0V

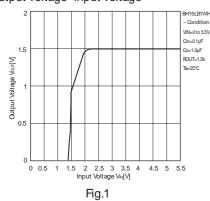
^{*} This product is not designed for protection against radio active rays.
*1 BH15, 18MA3WHFV: ±25 mV precision
*3 BH15, 18MA3WHFV: 3.0 to 5.5 V
*2 Excluding BH15, 18MA3WHFV
*4 BH15, 18MA3WHFV: 3.5 V

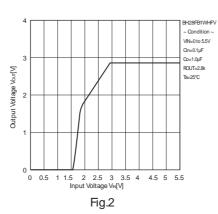
^{*1} BH \(\text{BH} \(\text{MA3WHFV: 1.0 } \psi F \)
*2 The output may become unstable at low temperatures and with light loads, so a capacitance of 2.2 \(\psi F \) or much more is recommended when using at low temperatures. (BH \(\text{BH} \) \| \text{FB1W})

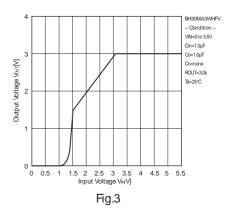
^{*3} Excluding BH15, 18LB1WHFV/WG *4 BH15, 18LB1WHFV/WG: VIN = 3.0 to 5.5 V

Typical characteristics

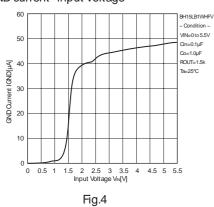
Output voltage-input voltage

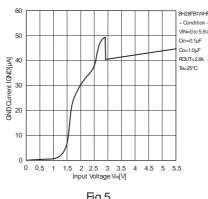






• GND current-input voltage





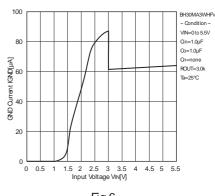
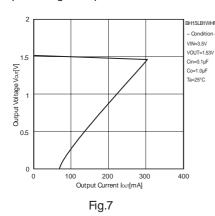
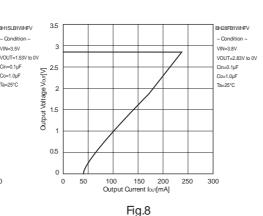


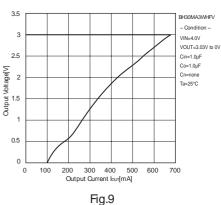
Fig.5

Fig.6

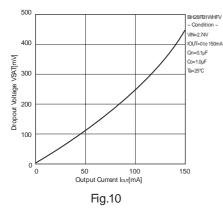
Output voltage-output current

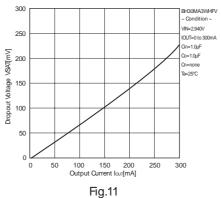






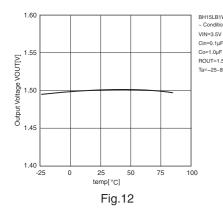
• Dropout voltage-output current

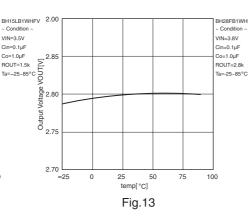


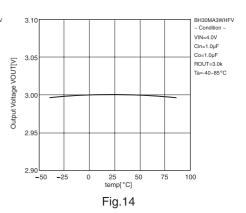


Typical Characteristics

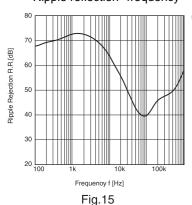
Output voltage-temperature

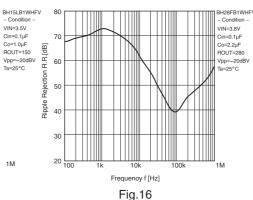


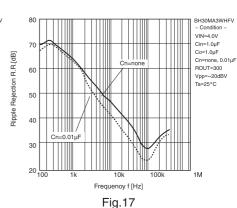


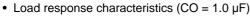


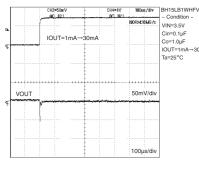
• Ripple reflection-frequency

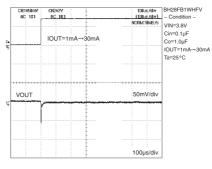












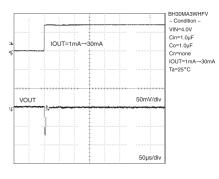
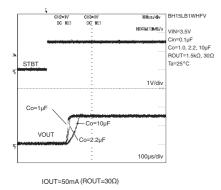


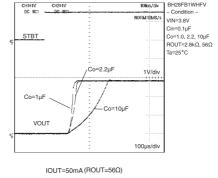
Fig.18

Fig.19

Fig.20

• Output voltage startup time





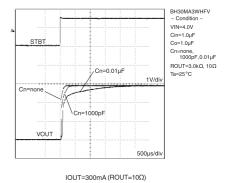
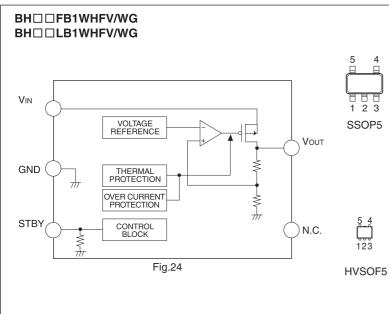


Fig.21

Fig.22

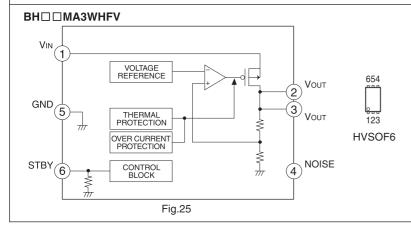
Fig.23

Block diagrams



PIN No.	Symbol	Function
1	Vin	Power supply input
2	GND	Ground
3	STBY	Output voltage ON/OFF control (High: ON, Low: OFF)
4	N. C.	NO CONNECT
5	Vouт	Voltage output

PIN No.	Symbol	Function
1	STBY	Output voltage ON/OFF control (High: ON, Low: OFF)
2	GND	Ground
3	VIN	Power supply input
4	Vout	Voltage output
5	N. C.	NO CONNECT



Terminal No.	Terminal Name	Function
1	Vin	Power supply input
2	Vоит	Voltage output
3	Vout	Voltage output
4	NOISE	Noise reducing capacitor ground terminal
5	GND	Ground
6	STBY	Output voltage ON/OFF control (High: ON, Low: OFF)

Power dissipation Pd

1. Power dissipation

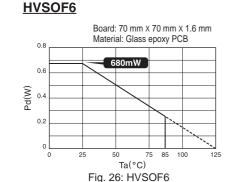
Power dissipation calculation include estimates of power dissipation characteristics and internal IC power consumption and should be treated as guidelines. In the event that the IC is used in an environment where this power dissipation is exceeded, the attendant rise in the junction temperature will trigger the thermal shutdown circuit, reducing the current capacity and otherwise degrading the IC's design performance. Allow for sufficient margins so that this power dissipation is not exceeded during IC operation.

Calculating the maximum internal IC power consumption (PMAX)

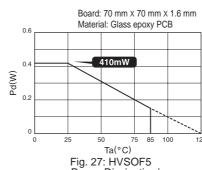
HVSOF5

PMAX=(VIN-VOUT) × IOUT(MAX.)

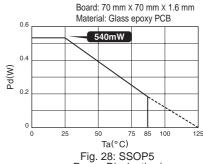
VIN: Input voltage
VOUT: Output voltage
IOUT(MAX.): Output current



Power Dissipation/
Power Dissipation Reduction (Example)



Power Dissipation/
Power Dissipation (Example)



SSOP5

Power Dissipation/
Power Dissipation Reduction (Example)

* Circuit design should allow a sufficient margin for the temperature range so that PMAX < Pd.

Input capacitor

It is recommended to insert bypass capacitors between input and GND pins, positioning them as close to the pins as possible. These capacitors will be used when the power supply impedance increases or when long wiring routes are used, so they should be checked once the IC has been mounted.

Ceramic capacitors generally have temperature and DC bias characteristics. When selecting ceramic capacitors, use X5R or X7R or better models that offer good temperature and DC bias characteristics and high torelant voltages.

Examples of ceramic capacitor characteristics

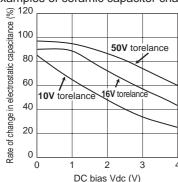


Fig. 29: Capacitance-bias characteristics (Y5V)

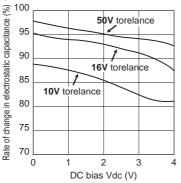


Fig. 30: Capacitance-bias characteristics (X5R, X7R)

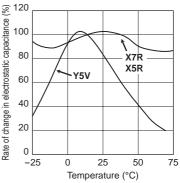


Fig. 31: Capacitance–temperature characteristics (X5R, X7R, Y5V)

Output capacitor

To prevent oscillation at the output, it is recommended that the IC be operated at the stable region show in below Fig. It operates at the capacitance of more than 1.0μF. As capacitance is larger, stability becomes more stable and characteristic of output load fluctuation is also improved.

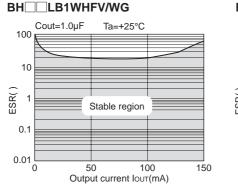


Fig. 32 BH LB1WHFV/WG Stable operating region characteristics (Example)

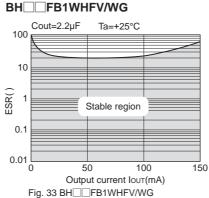


Fig. 33 BH FB1WHFV/WG
Stable operating region characteristics (Example)

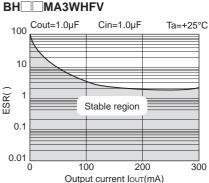


Fig. 34 BH MA3WHFV Stable operating region characteristics (Example)

Other precautions

· Over current protection circuit

The IC incorporates a built-in over current protection circuit that operates according to the output current capacity. This circuit serves to protect the IC from damage when the load is shorted. The protection circuits use fold-back type current limiting and are designed to limit current flow by not latching up in the event of a large and instantaneous current flow originating from a large capacitor or other component. These protection circuits are effective in preventing damage due to sudden and unexpected accidents. However, the IC should not be used in applications characterized by the continuous operation or transitioning of the protection circuits.

• Thermal shutdown circuit

This system has a built-in thermal shutdown circuit for the purpose of protecting the IC from thermal damage. As shown above, this must be used within the range of power dissipation, but if the power dissipation happens to be continuously exceeded, the chip temperature increases, causing the thermal shutdown circuit to operate. When the thermal shutdown circuit operates, the operation of the circuit is suspended. The circuit resumes operation immediately after the chip temperature decreases, so the output repeats the ON and OFF states. There are cases in which the IC is destroyed due to thermal runaway when it is left in the overloaded state. Be sure to avoid leaving the IC in the overloaded state.

Actions in strong magnetic fields

Use caution when using the IC in the presence of a strong magnetic field as such environments may occasionally cause the chip to malfunction.

Back current

In applications where the IC may be exposed to back current flow, it is recommended to create a route t dissipate this current by inserting a bypass diode between the VIN and VOUT pins.

GND potential

Ensure a minimum GND pin potential in all operating conditions.

In addition, ensure that no pins other than the GND pin carry a voltage less than or equal to the GND pin, including during actual transient phenomena.

The terminal is directly connected to inward normal voltage source. Because this has low current ability, load exceeding 100nA will cause some instability at the output. For such reasons, we urge you to use ceramic capacitors which have less leak current. When choosing noise the current reduction capacitor, there is a trade-off between boot-up time and stability. A bigger capacitor value will result in lesser oscillation but longer boot-up time for VOUT.

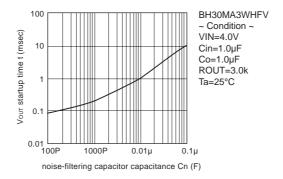


Fig. 35: Vout startup time vs. noise-filtering capacitor capacitance characteristics (Example)

Regarding input pin of the IC

This monolithic IC contains P+ isolation and P substrate layers between adjacent elements in order to keep them isolated. P/N junctions are formed at the intersection of these P layers with the N layers of other elements to create a variety of parasitic elements. For example, when a resistor and transistor are connected to pins as shown in Fig.37

- The P/N junction functions as a parasitic diode when GND > (Pin A) for the resistor or GND > (Pin B) for the transistor (NPN).
- Similarly, when GND > (Pin B) for the transistor (NPN), the parasitic diode described above combines with the N layer of other adjacent elements to operate as a parasitic NPN transistor.

The formation of parasitic elements as a result of the relationships of the potentials of different pins is an inevitable result of the IC's architecture. The operation of parasitic elements can cause interference with circuit operation as well as IC malfunction and damage. For these reasons, it is necessary to use caution so that the IC is not used in a way that will trigger the operation of parasitic elements, such as by the application of voltage lower than the GND (P substrate) voltage to input pins.

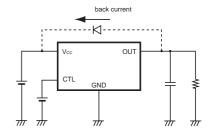
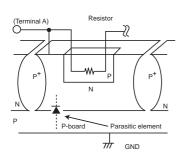
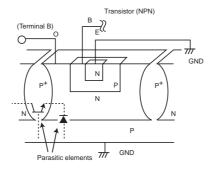


Fig. 36: Example of bypass diode connection





Other adjacent elements

Other adjacent elements

Other adjacent elements

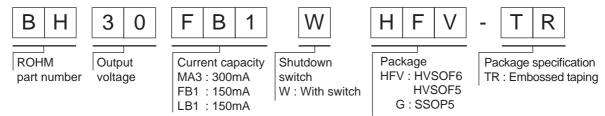
Parasitic element

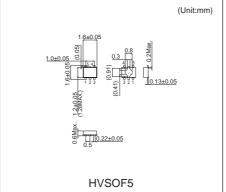
GND

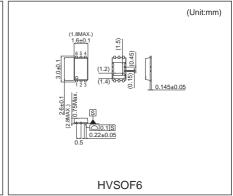
GND

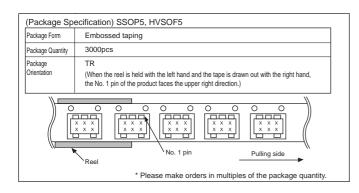
Fig.37

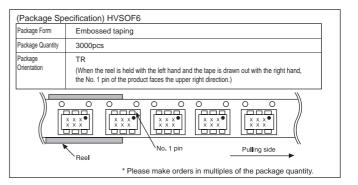
Part number selection











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The Products are not designed or manufactured to be used with any equipment, device or system which requires an extremely high level of reliability the failure or malfunction of which may result in a direct threat to human life or create a risk of human injury (such as a medical instrument, transportation equipment, aerospace machinery, nuclear-reactor controller, fuel-controller or other safety device). ROHM shall bear no responsibility in any way for use of any of the Products for the above special purposes. If a Product is intended to be used for any such special purpose, please contact a ROHM sales representative before purchasing.

If you intend to export or ship overseas any Product or technology specified herein that may be controlled under the Foreign Exchange and the Foreign Trade Law, you will be required to obtain a license or permit under the Law.



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